

Emanuele Rimini

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

248
papers

4,834
citations

33
h-index

58
g-index

257
ext. papers

5,041
ext. citations

2.9
avg, IF

4.85
L-index

#	Paper	IF	Citations
248	New insight into Pt nucleation mechanism on Si surface during galvanic displacement deposition. <i>Journal of Physics and Chemistry of Solids</i> , 2021 , 148, 109722	3.9	1
247	Crystallization of nano amorphized regions in thin epitaxial layer of Ge ₂ Sb ₂ Te ₅ . <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 194001	3	1
246	Disordering process of GeSb ₂ Te ₄ induced by ion irradiation. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 134001	3	1
245	Ion beam induced transient amorphous nucleation in silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2020 , 462, 130-138	1.2	1
244	Mechanical properties of amorphous Ge ₂ Sb ₂ Te ₅ thin layers. <i>Surface and Coatings Technology</i> , 2018 , 355, 227-233	4.4	8
243	Atomic diffusion in laser irradiated Ge rich GeSbTe thin films for phase change memory applications. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 145103	3	10
242	Atomic disordering processes in crystalline GeTe induced by ion irradiation. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 495103	3	3
241	Formation, Morphology, and Optical Properties of Electroless Deposited Gold Nanoparticles on 3C-SiC. <i>Journal of Physical Chemistry C</i> , 2017 , 121, 4304-4311	3.8	9
240	Chemical and structural arrangement of the trigonal phase in GeSbTe thin films. <i>Nanotechnology</i> , 2017 , 28, 065706	3.4	32
239	Influence of hydrofluoric acid treatment on electroless deposition of Au clusters. <i>Beilstein Journal of Nanotechnology</i> , 2017 , 8, 183-189	3	5
238	Crystallization properties of Sb-rich GeSbTe alloys by in-situ morphological and electrical analysis. <i>Materials Science in Semiconductor Processing</i> , 2017 , 65, 100-107	4.3	5
237	Strain Development and Damage Accumulation Under Ion Irradiation of Polycrystalline GeSbTe Alloys. <i>Nanoscience and Nanotechnology Letters</i> , 2017 , 9, 1095-1101	0.8	4
236	Phase Transitions in Ge-Sb-Te Alloys Induced by Ion Irradiations. <i>MRS Advances</i> , 2016 , 1, 2701-2709	0.7	2
235	Metal-Insulator Transition Driven by Vacancy Ordering in GeSbTe Phase Change Materials. <i>Scientific Reports</i> , 2016 , 6, 23843	4.9	77
234	Electrically Trimmable Phase Change Ge ₂ Sb ₂ Te ₅ Resistors With Tunable Temperature Coefficient of Resistance. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 2879-2885	2.9	3
233	Electroless Deposition of Silver Investigated with Rutherford Backscattering and Electron Microscopy. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, P235-P242	2	9
232	Transient crystal grain nucleation in As doped amorphous silicon. <i>Materials Letters</i> , 2014 , 126, 28-31	3.3	2

231	Investigation of Ag-Assisted Chemical Etching on (100) and (111) Contiguous Silicon Surfaces. <i>ECS Journal of Solid State Science and Technology</i> , 2013 , 2, P405-P412	2	12
230	Influence of substrate dielectric permittivity on local capacitive behavior in graphene. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012 , 44, 989-992	3	1
229	Ag-Assisted Chemical Etching of (100) and (111) n-Type Silicon Substrates by Varying the Amount of Deposited Metal. <i>Journal of the Electrochemical Society</i> , 2012 , 159, D521-D525	3.9	19
228	Micro- and Nano-Scale Electrical Characterization of Epitaxial Graphene on Off-Axis 4H-SiC (0001). <i>Materials Science Forum</i> , 2012 , 717-720, 637-640	0.4	4
227	Effect of graphene/4H-SiC(0 0 0 1) interface on electrostatic properties in graphene. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012 , 44, 993-996	3	1
226	Structural Characterization of Graphene Grown by Thermal Decomposition of Off-Axis 4H-SiC (0001). <i>Materials Science Forum</i> , 2012 , 711, 141-148	0.4	1
225	Crystallization of Nanometer Ge ₂ Sb ₂ Te ₅ Amorphous Regions Embedded in the Hexagonal Close Packed Structure. <i>Electrochemical and Solid-State Letters</i> , 2012 , 15, H105		5
224	Mapping the density of scattering centers limiting the electron mean free path in graphene. <i>Nano Letters</i> , 2011 , 11, 4612-8	11.5	84
223	Nucleation and grain growth in as deposited and ion implanted GeTe thin films. <i>Journal of Non-Crystalline Solids</i> , 2011 , 357, 2197-2201	3.9	19
222	Lateral homogeneity of the electronic properties in pristine and ion-irradiated graphene probed by scanning capacitance spectroscopy. <i>Nanoscale Research Letters</i> , 2011 , 6, 109	5	10
221	Local Electrical Properties of the 4H-SiC(0001)/Graphene Interface. <i>Materials Science Forum</i> , 2011 , 679-680, 769-776	0.4	2
220	Polymorphism of Amorphous Ge ₂ Sb ₂ Te ₅ Probed by EXAFS and Raman Spectroscopy. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H480		16
219	Amorphous-Crystal Phase Transitions in Ge _x Te _{1-x} Alloys. <i>Journal of the Electrochemical Society</i> , 2011 , 159, H130-H139	3.9	29
218	Selective diffusion of gold nanodots on nanopatterned substrates realized by self-assembly of diblock copolymers. <i>Journal of Materials Research</i> , 2011 , 26, 240-246	2.5	13
217	Ion Irradiation on Phase Change Materials. <i>Materials Research Society Symposia Proceedings</i> , 2011 , 1354, 73		1
216	Transport Properties of Graphene with Nanoscale Lateral Resolution. <i>Nanoscience and Technology</i> , 2011 , 247-285	0.6	8
215	Surface Corrugation and Stacking Misorientation in Multilayers of Graphene on Nickel. <i>Solid State Phenomena</i> , 2011 , 178-179, 125-129	0.4	1
214	Temperature Dependent Structural Evolution of Graphene Layers on 4H-SiC(0001). <i>Materials Science Forum</i> , 2011 , 679-680, 797-800	0.4	2

213	Crystallization of ion amorphized Ge ₂ Sb ₂ Te ₅ in nano-structured thin films. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1251, 3		2
212	Crystallization of ion amorphized Ge ₂ Sb ₂ Te ₅ thin films in presence of cubic or hexagonal phase. <i>Journal of Applied Physics</i> , 2010 , 107, 113521	2.5	19
211	Role of graphene/substrate interface on the local transport properties of the two-dimensional electron gas. <i>Applied Physics Letters</i> , 2010 , 97, 132101	3-4	54
210	Local Order and Crystallization of Laser Quenched and Ion Implanted Amorphous Ge _{1-x} Te _x Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1251, 8		
209	Local Order and Crystallization of Laser Quenched and Ion Implanted Amorphous Ge _{1-x} Te _x Thin Films. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H317		11
208	Amorphous-fcc transition in Ge ₂ Sb ₂ Te ₅ . <i>Microelectronic Engineering</i> , 2010 , 87, 294-300	2.5	18
207	Nanoscale capacitive behaviour of ion irradiated graphene on silicon oxide substrate. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 907-911	1.3	7
206	Investigation of graphene/SiC interface by nanoscale electrical characterization. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 912-915	1.3	9
205	Radiation pressure excitation and cooling of a cryogenic micro-mechanical systems cavity. <i>Journal of Applied Physics</i> , 2009 , 106, 013108	2.5	5
204	Low temperature formation and evolution of a 10 nm amorphous Ni ₃ Si layer on [001] silicon studied by in situ transmission electron microscopy. <i>Journal of Applied Physics</i> , 2009 , 105, 093506	2.5	12
203	Irradiation damage in graphene on SiO ₂ probed by local mobility measurements. <i>Applied Physics Letters</i> , 2009 , 95, 263109	3-4	30
202	Role of Ion Irradiation Induced Lattice Defects on Nanoscale Capacitive Behavior of Graphene. <i>Solid State Phenomena</i> , 2009 , 156-158, 305-311	0.4	
201	Amorphous to fcc-polycrystal transition in Ge ₂ Sb ₂ Te ₅ thin films studied by electrical measurements: Data analysis and comparison with direct microscopy observations. <i>Journal of Applied Physics</i> , 2009 , 105, 083546	2.5	13
200	Crystallization of sputtered-deposited and ion implanted amorphous Ge ₂ Sb ₂ Te ₅ thin films. <i>Journal of Applied Physics</i> , 2009 , 105, 123502	2.5	24
199	Evolution of the Transrotational Structure During Crystallization of Amorphous Ge ₂ Sb ₂ Te ₅ Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1160, 1		
198	Ion irradiation and defect formation in single layer graphene. <i>Carbon</i> , 2009 , 47, 3201-3207	10.4	186
197	Screening length and quantum capacitance in graphene by scanning probe microscopy. <i>Nano Letters</i> , 2009 , 9, 23-9	11.5	95
196	Crosstalk Characterization in Geiger-Mode Avalanche Photodiode Arrays. <i>IEEE Electron Device Letters</i> , 2008 , 29, 218-220	4.4	12

195	Interferometric Quantum Sensors. <i>Advances in Science and Technology</i> , 2008 , 55, 154-159	0.1	1
194	Ion irradiation-induced local structural changes in amorphous Ge ₂ Sb ₂ Te ₅ thin film. <i>Applied Physics Letters</i> , 2008 , 92, 241925	3.4	49
193	Electron programming and hole erasing in silicon nanocrystal Flash memories with fin field-effect transistor architecture. <i>Applied Physics Letters</i> , 2008 , 92, 203503	3.4	5
192	Single photon avalanche photodiodes arrays. <i>Sensors and Actuators A: Physical</i> , 2007 , 138, 306-312	3.9	23
191	Silicon Geiger mode avalanche photodiodes. <i>Optoelectronics Letters</i> , 2007 , 3, 177-180	0.7	3
190	Role of the internal strain on the incomplete Si ₃ BiO ₂ phase separation in substoichiometric silicon oxide films. <i>Applied Physics Letters</i> , 2007 , 90, 183101	3.4	20
189	Nucleation and growth of NiSi from Ni ₂ Si transrotational domains. <i>Applied Physics Letters</i> , 2007 , 90, 053507	3.07	9
188	Effects of mass, energy and temperature on amorphization in ion implanted Ge ₂ Sb ₂ Te ₅ thin films. <i>Materials Research Society Symposia Proceedings</i> , 2007 , 997, 1		1
187	Critical nickel thickness to form silicide transrotational structures on [001] silicon. <i>Applied Physics Letters</i> , 2006 , 89, 102105	3.4	18
186	Arrays of Geiger mode avalanche photodiodes. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 1633-1635	2.2	22
185	Structural characterization of Ni ₂ Si pseudoepitaxial transrotational structures on [001] Si. <i>Acta Crystallographica Section B: Structural Science</i> , 2006 , 62, 729-36		12
184	Test of scintillator readout with single photon avalanche photodiodes. <i>IEEE Transactions on Nuclear Science</i> , 2005 , 52, 3040-3046	1.7	8
183	Quantitative determination of the clustered silicon concentration in substoichiometric silicon oxide layer. <i>Applied Physics Letters</i> , 2005 , 87, 044102	3.4	24
182	Pseudoepitaxial transrotational structures in 14 nm-thick NiSi layers on [001] silicon. <i>Acta Crystallographica Section B: Structural Science</i> , 2005 , 61, 486-91		22
181	ImpuritiesBi interstitials interaction in Si doped with B or Ga during ion irradiation. <i>Journal of Physics Condensed Matter</i> , 2005 , 17, S2279-S2284	1.8	2
180	Cross section of the interaction between substitutional B and Si self-interstitials generated by ion beams. <i>Journal of Physics Condensed Matter</i> , 2005 , 17, S2273-S2277	1.8	2
179	Depth distribution of B implanted in Si after excimer laser irradiation. <i>Applied Physics Letters</i> , 2005 , 86, 051909	3.4	25
178	Lattice location and thermal evolution of small B complexes in crystalline Si. <i>Applied Physics Letters</i> , 2005 , 87, 201905	3.4	9

177	Crystal nucleation and growth processes in Ge ₂ Sb ₂ Te ₅ . <i>Applied Physics Letters</i> , 2004 , 84, 4448-4450	3.4	70
176	Amorphous-to-crystal transition of nitrogen- and oxygen-doped Ge ₂ Sb ₂ Te ₅ films studied by in situ resistance measurements. <i>Applied Physics Letters</i> , 2004 , 85, 3044-3046	3.4	180
175	Characterization of Embedded Rhomboidal Microchannels Formation on Silicon (100) Surface. <i>Journal of the Electrochemical Society</i> , 2004 , 151, C523	3.9	3
174	Electrical activation and lattice location of B and Ga impurities implanted in Si. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004 , 219-220, 727-731	1.2	1
173	Miniaturized proton exchange fuel cell in micromachined silicon surface 2004 , 5344, 163		
172	Silicon planar technology for single-photon optical detectors 2004 ,		1
171	Silicon planar technology for single-photon optical detectors. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 918-925	2.9	67
170	Memory effects in MOS devices based on Si quantum dots. <i>Materials Science and Engineering C</i> , 2003 , 23, 33-36	8.3	8
169	Crystallization and phase separation in Ge _{2+x} Sb ₂ Te ₅ thin films. <i>Journal of Applied Physics</i> , 2003 , 94, 4409-4413	6.2	1362
168	Peculiar aspects of nanocrystal memory cells: data and extrapolations. <i>IEEE Nanotechnology Magazine</i> , 2003 , 2, 319-323	2.6	13
167	Rapid thermal oxidation of epitaxial SiGe thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 89, 269-273	3.1	21
166	Location of holes in silicon-rich oxide as memory states. <i>Applied Physics Letters</i> , 2002 , 81, 3591-3593	3.4	3
165	Effects of N-induced heterogeneous nucleation and growth of cavities at the CoSi ₂ /polycrystalline Silicon interface. <i>Applied Physics Letters</i> , 2002 , 81, 55-57	3.4	9
164	Direct measurement of the growth rate during the C49 to C54 transformation in TiSi ₂ : Activation energy. <i>Journal of Applied Physics</i> , 2002 , 92, 627-628	2.5	13
163	Thermal oxidation of Si (001) single crystal implanted with Ge ions. <i>Journal of Applied Physics</i> , 2002 , 91, 6754	2.5	10
162	Kinetics of the C49 to C54 transformation by micro-Raman imaging. <i>Microelectronic Engineering</i> , 2001 , 55, 109-114	2.5	4
161	Silicon p ⁺ n junctions biased above breakdown used as monitors of carrier lifetime. <i>Materials Science in Semiconductor Processing</i> , 2001 , 4, 159-161	4.3	1
160	Si:Er:O layers grown by molecular beam epitaxy: structural, electrical and optical properties. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001 , 81, 62-66	3.1	2

159	Structural relationship of polycrystalline cobalt silicide lines to (001) silicon substrate and their thermal stability. <i>Microelectronic Engineering</i> , 2001 , 55, 163-169	2.5	7
158	Simulation of the transformation from the C49 to the C54 phase of TiSi ₂ in blanket films and narrow conductors. <i>Applied Physics Letters</i> , 2001 , 78, 1514-1516	3.4	4
157	In situ sensor for interstitial trapping during Si thermal oxidation using He implantation-induced voids. <i>Applied Physics Letters</i> , 2001 , 79, 3959-3961	3.4	6
156	Improvement of CoSi ₂ thermal stability by cavity formation. <i>Applied Physics Letters</i> , 2001 , 79, 3419-3421	3.4	8
155	Photoluminescence and structural studies on extended defect evolution during high-temperature processing of ion-implanted epitaxial silicon. <i>Journal of Applied Physics</i> , 2001 , 89, 4310-4317	2.5	9
154	Evidence for small interstitial clusters as the origin of photoluminescence W band in ion-implanted silicon. <i>Applied Physics Letters</i> , 2001 , 78, 291-293	3.4	39
153	Investigation on C54 nucleation and growth by micro-Raman imaging. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 611, 1		
152	Formation and annealing of defects during high-temperature processing of ion-implanted epitaxial silicon: the role of dopant implants. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000 , 71, 186-191	3.1	12
151	Determination of C54 nucleation site density in narrow stripes by sheet resistance measurements and Raman spectroscopy. <i>Microelectronic Engineering</i> , 2000 , 50, 139-145	2.5	7
150	Effect of lateral dimensional scaling on the thermal stability of poly-CoSi ₂ reacted on Si (001). <i>Microelectronic Engineering</i> , 2000 , 50, 179-186	2.5	
149	Voids in Silicon by He Implantation: From Basic to Applications. <i>Journal of Materials Research</i> , 2000 , 15, 1449-1477	2.5	130
148	Thermal Oxidation of High Dose Aluminum Implanted Silicon. <i>Journal of the Electrochemical Society</i> , 2000 , 147, 2762	3.9	2
147	Effect of O:Er concentration ratio on the structural, electrical, and optical properties of Si:Er:O layers grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2000 , 88, 4091	2.5	26
146	Oxidation induced precipitation in Al implanted epitaxial silicon. <i>Journal of Applied Physics</i> , 2000 , 88, 3988	2.5	1
145	Nucleation and growth of C54 grains into C49 TiSi ₂ thin films monitored by micro-Raman imaging. <i>Journal of Applied Physics</i> , 2000 , 88, 7013-7019	2.5	18
144	Structural relationship of polycrystalline cobalt silicide lines to (001) silicon substrate. <i>Applied Physics Letters</i> , 1999 , 75, 2924-2926	3.4	4
143	Thermal stability of cobalt silicide stripes on Si (001). <i>Journal of Applied Physics</i> , 1999 , 86, 3089-3095	2.5	20
142	Ni-Induced Selective Nucleation and Solid Phase Epitaxy of Large-Grained Poly-Si on Glass. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 587, O8.1.1		

141	Voids in silicon power devices. <i>Solid-State Electronics</i> , 1998 , 42, 2295-2301	1.7	14
140	Roughness of thermal oxide layers grown on ion implanted silicon wafers. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998 , 16, 619		13
139	Arsenic redistribution at the SiO ₂ /Si interface during oxidation of implanted silicon. <i>Physical Review B</i> , 1998 , 58, 10990-10999	3.3	11
138	Effect of the linewidth reduction on the characteristic time spread in C49 α 54 phase transition. <i>Applied Physics Letters</i> , 1998 , 73, 3863-3865	3.4	20
137	Precipitation of As in thermally oxidized ion-implanted Si crystals. <i>Applied Physics Letters</i> , 1998 , 73, 2633-2635	3.8	8
136	Hole mobility in aluminium implanted silicon. <i>Semiconductor Science and Technology</i> , 1997 , 12, 1433-1437	1.8	6
135	Interaction and Migration Properties of Ion Beam Induced Point Defects in Crystalline Silicon: Basic Research and Technological Relevance. <i>Defect and Diffusion Forum</i> , 1997 , 153-155, 137-158	0.7	5
134	Electrical characterization of ultra-shallow junctions formed by diffusion from a CoSi ₂ /sub 2/ layer. <i>IEEE Transactions on Electron Devices</i> , 1997 , 44, 526-534	2.9	30
133	Laser annealing of silicon. <i>Materials Chemistry and Physics</i> , 1996 , 46, 169-177	4.4	32
132	Arsenic and boron diffusion in silicon from implanted cobalt silicide layers. <i>Semiconductor Science and Technology</i> , 1995 , 10, 1362-1367	1.8	8
131	Radiation Damage 1995 , 131-172		
130	Annealing and Secondary Defects 1995 , 173-216		2
129	Experimental analysis of high energy boron implantation in silicon. <i>Radiation Effects and Defects in Solids</i> , 1994 , 129, 133-139	0.9	7
128	Channeling implants in silicon crystals. <i>Materials Chemistry and Physics</i> , 1994 , 38, 105-130	4.4	16
127	Al-O interactions in ion-implanted crystalline silicon. <i>Journal of Applied Physics</i> , 1994 , 76, 2070-2077	2.5	14
126	Diffusion and outdiffusion of aluminium implanted into silicon. <i>Semiconductor Science and Technology</i> , 1993 , 8, 488-494	1.8	25
125	Electrical characterization of polycrystalline silicon films on Si substrates processed by rapid thermal annealing. <i>Semiconductor Science and Technology</i> , 1993 , 8, 327-332	1.8	2
124	Size effects in the epitaxial realignment of polycrystalline silicon films onto Si substrates. <i>Applied Physics Letters</i> , 1993 , 62, 1895-1897	3.4	2

123	Two-dimensional distributions of ions implanted in channeling and random directions of Si single crystals. <i>Journal of Applied Physics</i> , 1993 , 74, 2370-2377	2.5	9
122	Al-O complex formation in ion implanted Czochralski and floating-zone Si substrates. <i>Applied Physics Letters</i> , 1993 , 62, 393-395	3.4	18
121	Al-Based Precipitate Evolution during High Temperature Annealing of Al Implanted in Si. <i>Journal of the Electrochemical Society</i> , 1993 , 140, 2313-2318	3.9	12
120	Diffusion and precipitation of As from a CoSi ₂ diffusion source. <i>Applied Surface Science</i> , 1993 , 73, 175-181	4.7	5
119	Structural and electrical study of epitaxially realigned Sb-doped polycrystalline Si films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1993 , 18, 289-294	3.1	
118	Direct-energy processes and phase transitions in silicon. <i>Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics</i> , 1993 , 15, 399-414		1
117	Kinetic and structural study of the epitaxial realignment of polycrystalline Si films. <i>Journal of Applied Physics</i> , 1992 , 71, 638-647	2.5	14
116	Lateral straggling of B and P ions implanted in channeling and random directions of Si single crystals. <i>Applied Physics Letters</i> , 1992 , 61, 1190-1192	3.4	2
115	Amorphous-crystal silicon interfaces: structure and movement under ion beam irradiation. <i>Applied Surface Science</i> , 1992 , 56-58, 577-588	6.7	33
114	Structural characterization of the epitaxial realignment of polycrystalline silicon films. <i>Materials Chemistry and Physics</i> , 1992 , 32, 99-105	4.4	4
113	Concentration profiles and electrical characterization of high energy phosphorus implants in <100> silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1991 , 10, 67-73	3.1	3
112	Epitaxial realignment of polycrystalline Si layers by rapid thermal annealing. <i>Microelectronic Engineering</i> , 1991 , 15, 143-146	2.5	
111	Titanium silicide as a diffusion source for phosphorous: precipitation and activation. <i>Applied Surface Science</i> , 1991 , 53, 190-195	6.7	8
110	Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus. <i>Applied Surface Science</i> , 1991 , 53, 377-382	6.7	6
109	Realignment of As doped silicon films deposited on silicon substrates. <i>Semiconductor Science and Technology</i> , 1991 , 6, 850-856	1.8	8
108	Precipitation of arsenic diffused into silicon from a TiSi ₂ source. <i>Journal of Applied Physics</i> , 1991 , 69, 7262-7271	3.1	14
107	High-energy channeling implants of phosphorus along the silicon. <i>Physical Review B</i> , 1991 , 44, 10568-10577	3.7	19
106	Realignment of As doped polycrystalline Si films by double step annealing. <i>Applied Physics Letters</i> , 1991 , 59, 2507-2509	3.4	7

105	Channeling implants of B ions into silicon surfaces. <i>Radiation Effects and Defects in Solids</i> , 1991 , 116, 211-217	0.9	17
104	Extended defect removal in silicon by rapid thermal annealing. <i>Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics</i> , 1990 , 12, 1593-1601		2
103	Optical evidence of precipitates in arsenic-implanted silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1990 , 5, 229-232	3.1	
102	Arsenic redistribution and out-diffusion in TiSi ₂ -Si bilayered structures. <i>Semiconductor Science and Technology</i> , 1990 , 5, 831-835	1.8	2
101	Boron implants in silicon at tilt angles of 0 degrees and 7 degrees. <i>Semiconductor Science and Technology</i> , 1990 , 5, 1007-1012	1.8	14
100	High breakdown-voltage diodes produced by multiple MeV B implants. <i>Semiconductor Science and Technology</i> , 1990 , 5, 653-656	1.8	
99	Infrared study of Fe-B-pair behavior in iron-implanted Czochralski silicon. <i>Journal of Applied Physics</i> , 1990 , 67, 3538-3541	2.5	
98	Low-temperature reordering in partially amorphized Si crystals. <i>Applied Physics Letters</i> , 1990 , 57, 768-770	9.4	22
97	Concentration dependence and interfacial instabilities during ion beam annealing of arsenic-doped silicon. <i>Applied Physics Letters</i> , 1990 , 56, 24-26	3.4	7
96	Phenomenological description of ion-beam-induced epitaxial crystallization of amorphous silicon. <i>Physical Review B</i> , 1990 , 41, 5235-5242	3.3	64
95	Titanium silicide as a diffusion source for arsenic. <i>Journal of Applied Physics</i> , 1990 , 67, 7174-7176	2.5	6
94	Ion-induced annealing and amorphization of isolated damage clusters in Si. <i>Applied Physics Letters</i> , 1990 , 56, 2622-2624	3.4	30
93	Arsenic influence on extended defects produced in silicon by ion implantation. <i>Applied Physics Letters</i> , 1990 , 56, 2405-2407	3.4	3
92	Ion-beam-induced epitaxial crystallization and amorphization in silicon. <i>Materials Science and Engineering Reports</i> , 1990 , 5, 319-379		186
91	Ion-beam-induced epitaxial crystallization and amorphization in silicon. <i>Materials Science and Engineering Reports</i> , 1990 , 5, 321-379		21
90	Influence of oxygen on the ion-assisted regrowth of deposited Si layers. <i>Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics</i> , 1989 , 11, 1805-1818		5
89	Implants of 15B0 MeV Boron ions into silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989 , 2, 69-73	3.1	24
88	Ion-assisted recrystallization of amorphous silicon. <i>Applied Surface Science</i> , 1989 , 43, 178-186	6.7	28

87	Dependence of PtSi Schottky diode electrical behaviour on the platinum film thickness and on the annealing process. <i>Thin Solid Films</i> , 1988 , 161, 13-20	2.2	7
86	Reflectancevs. Electroreflectance measurements on arsenic-doped silicon crystal. <i>Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics</i> , 1988 , 10, 979-988		2
85	A metastable NiSi phase epitaxially grown on <111> silicon by pulsed laser quenching. <i>Journal of the Less Common Metals</i> , 1988 , 145, 181-187		1
84	Influence of a thin interfacial oxide layer on the ion beam assisted epitaxial crystallization of deposited Si. <i>Applied Physics Letters</i> , 1988 , 53, 2605-2607	3.4	25
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